

# MOSFET – N-Channel DUAL COOL<sup>®</sup> 88 POWERTRENCH<sup>®</sup>

## 80 V, 254 A, 1.35 mΩ

### FDMT80080DC

#### Description

This N-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process. Advancements in both silicon and DUAL COOL package technologies have been combined to offer the lowest  $R_{DS(on)}$  while maintaining excellent switching performance by extremely low Junction-to-Ambient thermal resistance.

#### Features

- Max  $R_{DS(on)}$  = 1.35 mΩ at  $V_{GS}$  = 10 V,  $I_D$  = 36 A
- Max  $R_{DS(on)}$  = 1.82 mΩ at  $V_{GS}$  = 8 V,  $I_D$  = 31 A
- Advanced Package and Silicon Combination for Low  $R_{DS(on)}$  and High Efficiency
- Next Generation Enhanced Body diode technology, Engineered for Soft recovery
- Low profile 8x8mm MLP package
- MSL1 Robust Package Design
- 100% UIL tested
- These Device is Pb-Free, Halide Free, and is RoHS Compliant

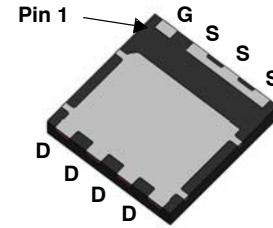
#### Typical Applications

- OringFET / Load Switching
- Synchronous Rectification
- DC-DC Conversion

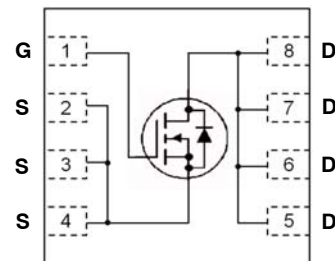
#### MOSFET MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                                                                                                                                                                 | Value                    | Unit             |
|----------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------|------------------|
| $V_{DS}$       | Drain to Source Voltage                                                                                                                                                                   | 80                       | V                |
| $V_{GS}$       | Gate to Source Voltage                                                                                                                                                                    | $\pm 20$                 | V                |
| $I_D$          | Drain Current<br>– Continuous $T_C = 25^\circ\text{C}$ (Note 5)<br>– Continuous $T_C = 100^\circ\text{C}$ (Note 5)<br>– Continuous $T_A = 25^\circ\text{C}$ (Note 1)<br>– Pulsed (Note 4) | 254<br>160<br>36<br>1453 | A                |
| $E_{AS}$       | Single Pulse Avalanche Energy (Note 3)                                                                                                                                                    | 1734                     | mJ               |
| $P_D$          | Power Dissipation $T_C = 25^\circ\text{C}$<br>Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1)                                                                                         | 156<br>3.2               | W                |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range                                                                                                                                          | $-55$ to $+150$          | $^\circ\text{C}$ |

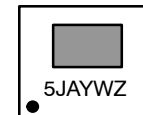
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



PQFN8 8X8, 2P  
CASE 483AQ



#### MARKING DIAGRAM



- 5J = Specific Device Code  
A = Assembly Plant Code  
YW = Data Code (Year & Week)  
Z = Lot Code

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

# FDMT80080DC

## ELECTRICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

### Off Characteristics

|                                      |                                           |                                                             |    |    |     |                      |
|--------------------------------------|-------------------------------------------|-------------------------------------------------------------|----|----|-----|----------------------|
| $BV_{DSS}$                           | Drain to Source Breakdown Voltage         | $I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$           | 80 | –  | –   | V                    |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$ | –  | 41 | –   | mV/ $^\circ\text{C}$ |
| $I_{DSS}$                            | Zero Gate Voltage Drain Current           | $V_{DS} = 64\ \text{V}$ , $V_{GS} = 0\ \text{V}$            | –  | –  | 1   | $\mu\text{A}$        |
| $I_{GSS}$                            | Gate to Source Leakage Current            | $V_{GS} = \pm 20\ \text{V}$ , $V_{DS} = 0\ \text{V}$        | –  | –  | 100 | nA                   |

### On Characteristics

|                                        |                                                          |                                                                                                                                                                                 |             |                      |                      |                      |
|----------------------------------------|----------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------|----------------------|----------------------|----------------------|
| $V_{GS(th)}$                           | Gate to Source Threshold Voltage                         | $V_{GS} = V_{DS}$ , $I_D = 250\ \mu\text{A}$                                                                                                                                    | 2.0         | 3.1                  | 4.0                  | V                    |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$                                                                                                                     | –           | –12                  | –                    | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$                           | Static Drain–Source On–Resistance                        | $V_{GS} = 10\ \text{V}$ , $I_D = 36\ \text{A}$<br>$V_{GS} = 8\ \text{V}$ , $I_D = 31\ \text{A}$ ,<br>$V_{GS} = 10\ \text{V}$ , $I_D = 36\ \text{A}$ , $T_J = 125^\circ\text{C}$ | –<br>–<br>– | 1.06<br>1.23<br>1.74 | 1.35<br>1.82<br>2.22 | m $\Omega$           |
| $g_{FS}$                               | Forward Transconductance                                 | $V_{DS} = 5\ \text{V}$ , $I_D = 36\ \text{A}$                                                                                                                                   | –           | 116                  | –                    | S                    |

### Dynamic Characteristics

|           |                              |                                                                        |     |       |       |          |
|-----------|------------------------------|------------------------------------------------------------------------|-----|-------|-------|----------|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 40\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$ | –   | 14800 | 20720 | pF       |
| $C_{oss}$ | Output Capacitance           |                                                                        | –   | 2080  | 2915  | pF       |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                        | –   | 56    | 125   | pF       |
| $R_g$     | Gate Resistance              |                                                                        | 0.1 | 1.8   | 4.5   | $\Omega$ |

### Switching Characteristics

|              |                               |                                                                                                     |   |     |     |    |
|--------------|-------------------------------|-----------------------------------------------------------------------------------------------------|---|-----|-----|----|
| $t_{d(on)}$  | Turn–On Delay Time            | $V_{DD} = 40\ \text{V}$ , $I_D = 36\ \text{A}$ ,<br>$V_{GS} = 10\ \text{V}$ , $R_{GEN} = 6\ \Omega$ | – | 67  | 108 | ns |
| $t_r$        | Rise Time                     |                                                                                                     | – | 65  | 104 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time           |                                                                                                     | – | 75  | 120 | ns |
| $t_f$        | Fall Time                     |                                                                                                     | – | 30  | 48  | ns |
| $Q_{g(TOT)}$ | Total Gate Charge             | $V_{GS} = 0\ \text{V}$ , to $10\ \text{V}$ ,<br>$V_{DD} = 40\ \text{V}$ , $I_D = 36\ \text{A}$      | – | 195 | 273 | nC |
|              | Total Gate Charge             | $V_{GS} = 0\ \text{V}$ , to $8\ \text{V}$ ,<br>$V_{DD} = 40\ \text{V}$ , $I_D = 36\ \text{A}$       | – | 159 | 223 | nC |
| $Q_{gs}$     | Gate to Source Charge         | $V_{DD} = 40\ \text{V}$ , $I_D = 36\ \text{A}$                                                      | – | 69  | –   | nC |
| $Q_{gd}$     | Gate to Drain “Miller” Charge |                                                                                                     | – | 36  | –   | nC |

### Drain–Source Diode Characteristics

|          |                                       |                                                            |   |     |     |    |
|----------|---------------------------------------|------------------------------------------------------------|---|-----|-----|----|
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS} = 0\ \text{V}$ , $I_S = 2.6\ \text{A}$ (Note 2)    | – | 0.7 | 1.1 | V  |
|          |                                       | $V_{GS} = 0\ \text{V}$ , $I_S = 36\ \text{A}$ (Note 2)     | – | 0.8 | 1.2 |    |
| $t_{rr}$ | Reverse Recovery Time                 | $I_F = 36\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$ | – | 81  | 130 | ns |
| $Q_{rr}$ | Reverse Recovery Charge               |                                                            | – | 88  | 141 | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

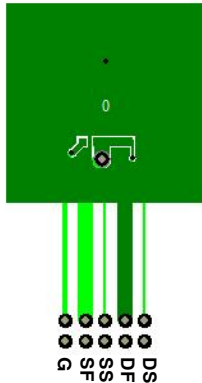


# THERMAL CHARACTERISTICS

| Symbol          | Parameter                                           | Value | Unit                 |
|-----------------|-----------------------------------------------------|-------|----------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Top Source)   | 1.6   | $^{\circ}\text{C/W}$ |
|                 | Thermal Resistance, Junction-to-Case (Bottom Drain) | 0.8   |                      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a)   | 38    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1b)   | 81    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1c)   | 26    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1d)   | 34    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1e)   | 14    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1f)   | 16    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1g)   | 26    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1h)   | 60    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1i)   | 15    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1j)   | 21    |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1k)   | 9     |                      |
|                 | Thermal Resistance, Junction-to-Ambient (Note 1l)   | 11    |                      |

## NOTES:

- $R_{\theta JA}$  is determined with the device mounted on a FR-4 board using a specified pad of 2 oz copper as shown below.  $R_{\theta CA}$  is determined by the user's board design.



a) 38  $^{\circ}\text{C/W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b) 81  $^{\circ}\text{C/W}$  when mounted on a minimum pad of 2 oz copper.

- Still air, 20.9 x 10.4 x 12.7 mm Aluminum Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
  - Still air, 20.9 x 10.4 x 12.7 mm Aluminum Heat Sink, minimum pad of 2 oz copper
  - Still air, 45.2 x 41.4 x 11.7 mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
  - Still air, 45.2 x 41.4 x 11.7 mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper
  - 200FPM Airflow, No Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
  - 200FPM Airflow, No Heat Sink, minimum pad of 2 oz copper
  - 200FPM Airflow, 20.9 x 10.4 x 12.7 mm Aluminum Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
  - 200FPM Airflow, 20.9 x 10.4 x 12.7 mm Aluminum Heat Sink, minimum pad of 2 oz copper
  - 200FPM Airflow, 45.2 x 41.4 x 11.7 mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
  - 200FPM Airflow, 45.2 x 41.4 x 11.7 mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper
- Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty Cycle < 2.0%.
  - $E_{AS}$  of 1734 mJ is based on starting  $T_J = 25^{\circ}\text{C}$ ,  $L = 3 \text{ mH}$ ,  $I_{AS} = 34 \text{ A}$ ,  $V_{DD} = 80 \text{ V}$ ,  $V_{GS} = 10 \text{ V}$ . 100% test at  $L = 0.3 \text{ mH}$ ,  $I_{AS} = 75 \text{ A}$
  - Pulsed Id please refer to Figure 11 SOA graph for more details.
  - Computed Continuous Current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.



TYPICAL CHARACTERISTICS  $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED

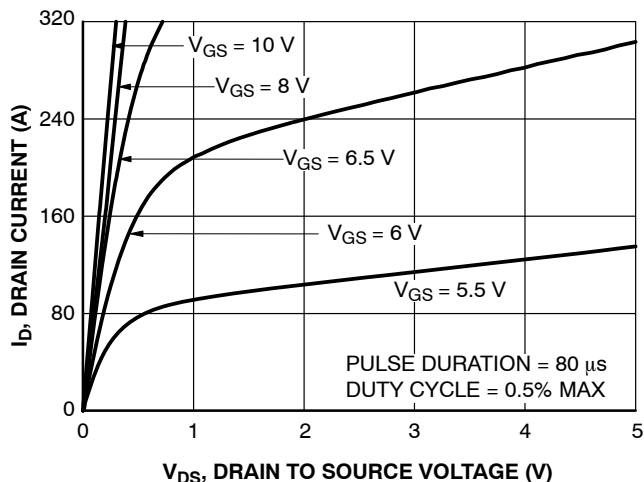


Figure 1. On-Region Characteristics

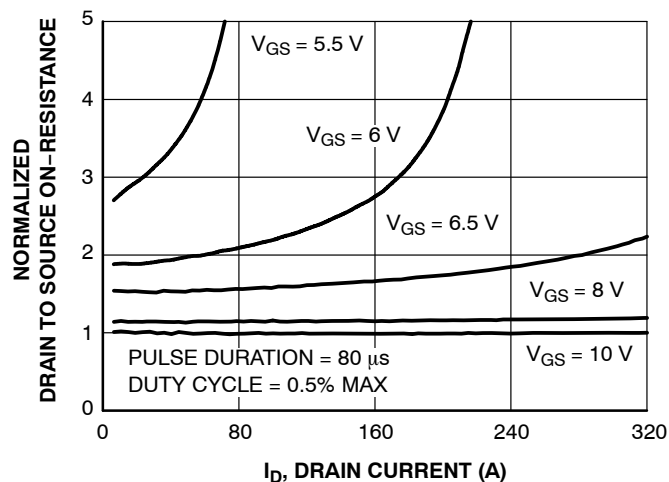


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

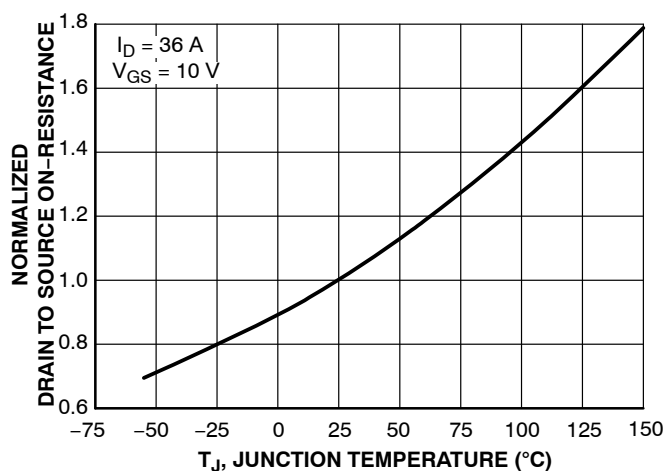


Figure 3. Normalized On Resistance vs. Junction Temperature

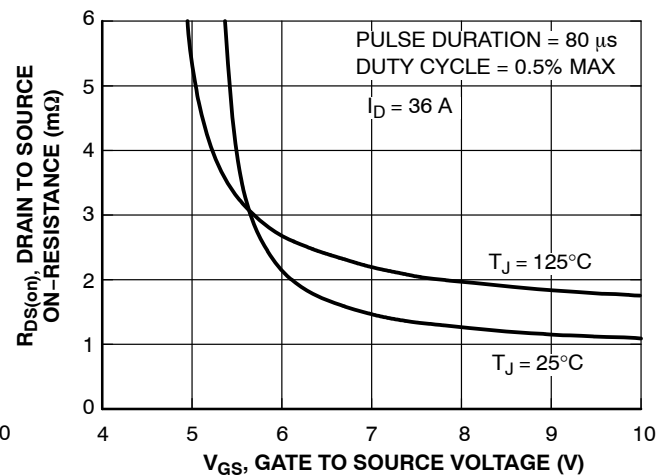


Figure 4. On Resistance vs. Gate to Source Voltage

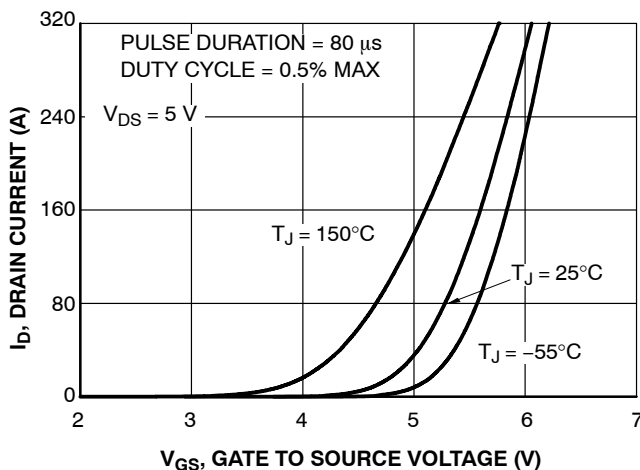


Figure 5. Transfer Characteristics

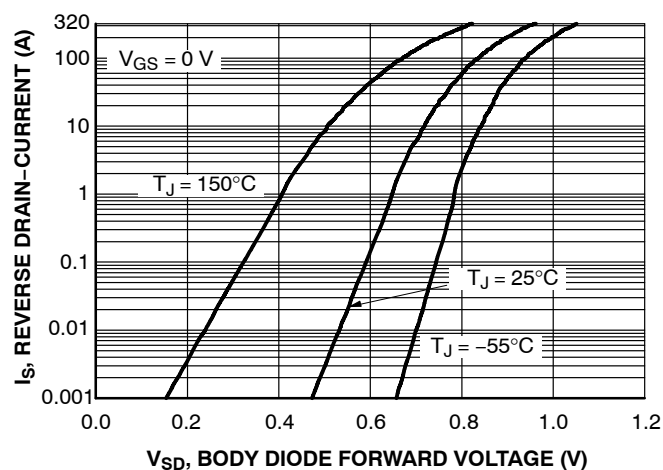


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (CONTINUED)  $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED

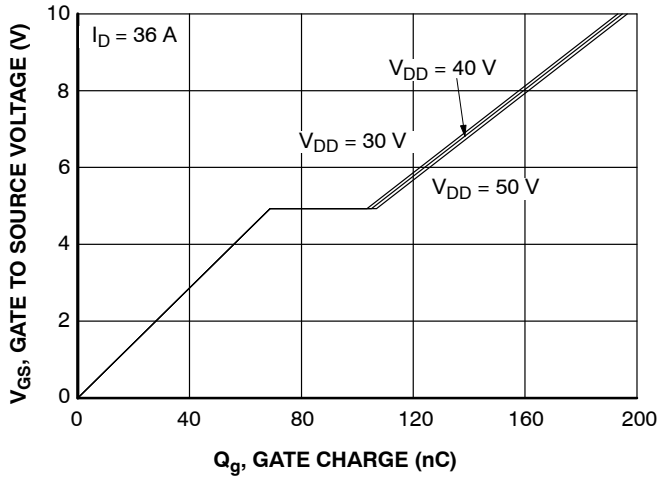


Figure 7. Gate Charge Characteristics

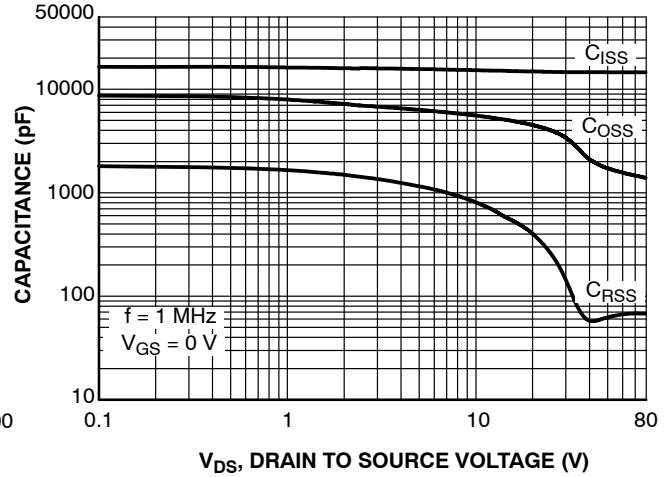


Figure 8. Capacitance vs. Drain to Source Voltage

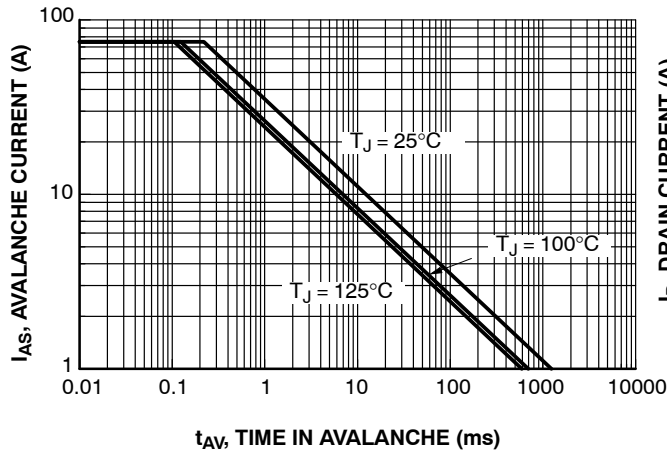


Figure 9. Unclamped Inductive Switching Capability

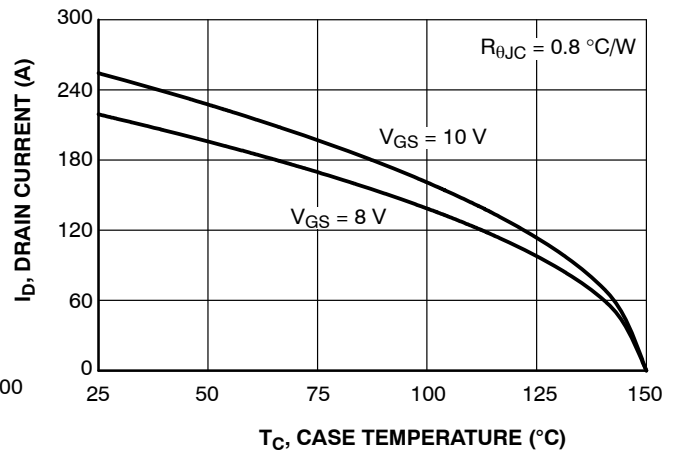


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

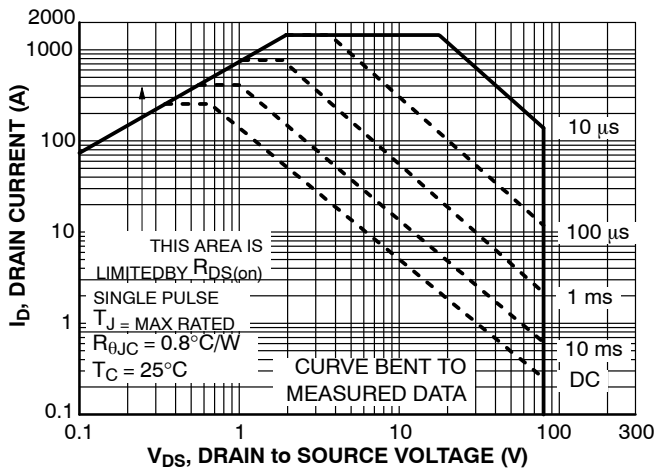


Figure 11. Forward Bias Safe Operating Area

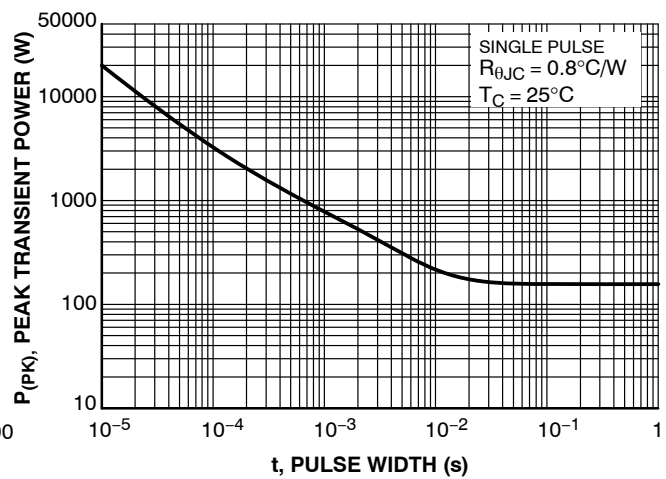


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (CONTINUED)  $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED

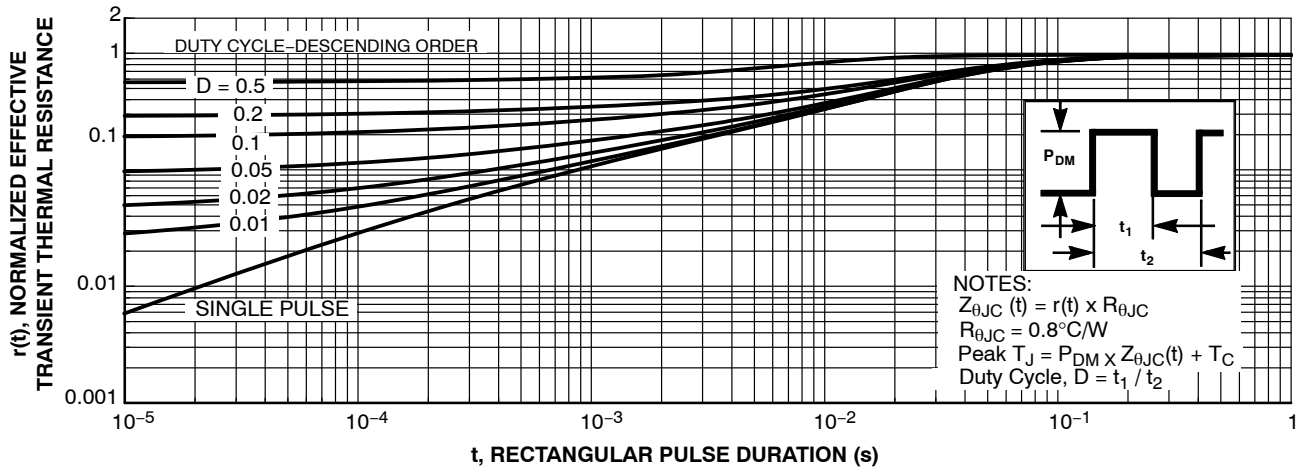
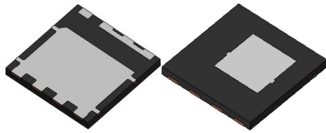


Figure 13. Junction-to-Case Transient Thermal Response Curve

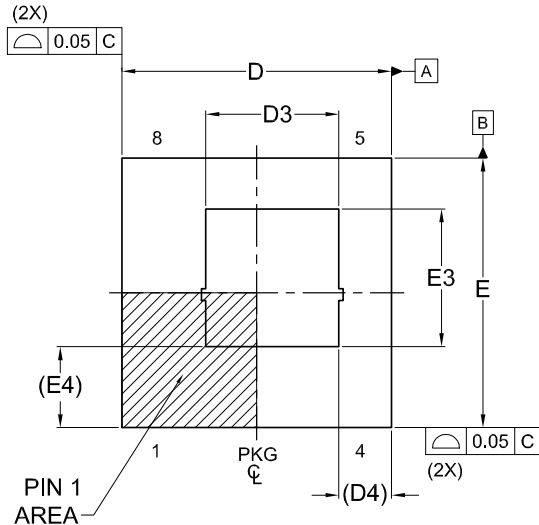
ORDERING INFORMATION

| Device Marking | Device      | Package      | Reel Size | Tape Width | Shipping (Qty / Packing) <sup>†</sup> |
|----------------|-------------|--------------|-----------|------------|---------------------------------------|
| 5J             | FDMT80080DC | Dual Cool™88 | 13"       | 13.3 mm    | 3000 / Tape & Reel                    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

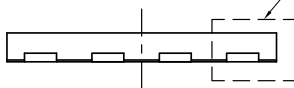

**PQFN8 8X8, 2P**  
**CASE 483AQ**  
**ISSUE B**

DATE 24 OCT 2022

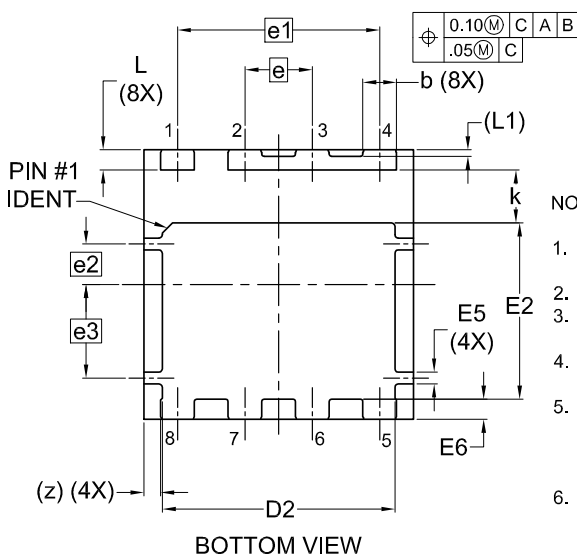


TOP VIEW

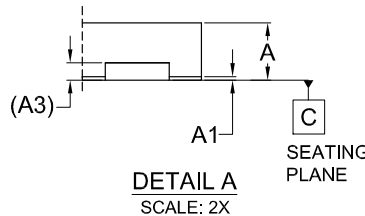
SEE DETAIL A



FRONT VIEW

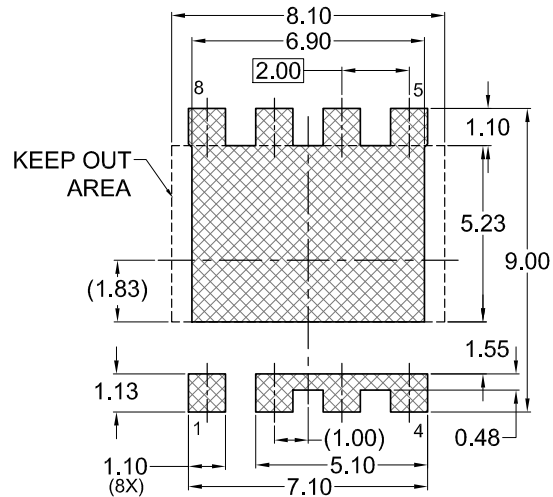


BOTTOM VIEW



## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.


LAND PATTERN  
RECOMMENDATION

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN.        | NOM. | MAX. |
| A   | 0.75        | 0.85 | 0.95 |
| A1  | 0.00        | -    | 0.05 |
| A3  | 0.25 REF    |      |      |
| b   | 0.90        | 1.00 | 1.10 |
| D   | 7.90        | 8.00 | 8.10 |
| D2  | 6.80        | 6.90 | 7.00 |
| D3  | 3.68        | 3.86 | 4.03 |
| D4  | 1.56 REF    |      |      |
| E   | 7.90        | 8.00 | 8.10 |
| E2  | 5.13        | 5.23 | 5.33 |
| E3  | 3.99        | 4.09 | 4.19 |
| E4  | 2.41 REF    |      |      |
| E5  | 0.35 REF    |      |      |
| E6  | 0.60 REF    |      |      |
| e   | 2.00 BSC    |      |      |
| e1  | 6.00 BSC    |      |      |
| e2  | 1.20 BSC    |      |      |
| e3  | 2.78 BSC    |      |      |
| k   | 1.48        | 1.58 | 1.68 |
| L   | 0.50        | 0.60 | 0.70 |
| L1  | 0.20 REF    |      |      |
| z   | 0.50 REF    |      |      |

**DOCUMENT NUMBER:** 98AON13665G

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**DESCRIPTION:** PQFN8 8X8, 2P

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